AMENDMENTS TO THE CLAIMS

1. (currently amended) A composition suitable for use as a planarizing underlayer in a multilayer lithographic process, said composition comprising:

(a) a polymer containing:

(i) epoxy~~cyclic ether~~ moieties,

(ii) saturated fused polycyclic hydrocarbon moieties, ~~and~~

(iii) aromatic moieties, and

(iv) fluorine-containing moieties, and

(b) an acid generator.

2. (currently amended) The composition of claim 1 wherein said epoxy~~cyclic ether~~ moieties are pendant from acrylate monomers, said monomers forming at least a portion of said polymer.

3. (currently amended) The composition of claim 1 wherein said fused polycyclic hydrocarbon moieties are pendant from acrylate monomers, said monomers forming at least a portion of said polymer.

4. (currently amended) The composition of claim 1 wherein said fused polycyclic hydrocarbon moieties are located in a backbone portion of said polymer.

5. (original) The composition of claim 1 wherein said aromatic moieties are pendant from an ethylenic monomer, said monomer forming at least a portion of said polymer.

6. (original) The composition of claim 5 wherein said aromatic moieties are selected from the group consisting of phenyl and phenol.

7. (currently amended) The composition of claim 1 wherein said polymer contains acrylate monomers having both ~~an~~a fused polycyclic hydrocarbon moiety and ~~a cyclic ether~~ an epoxy moiety pendant from said monomer.

8. (original) The composition of claim 1 wherein said acid generator is a thermally activated acid generator.

9. (canceled)

10. (original) The composition of claim 1 wherein said composition consists essentially of components (a) and (b).

11. (currently amended) A lithographic structure on a substrate, said structure comprising:

(a) a planarizing underlayer comprising:

a polymer containing:

(i) epoxy~~cyclic ether~~ moieties,

(ii) saturated fused polycyclic hydrocarbon moieties, ~~and~~

(iii) aromatic moieties, and

an acid generator.

(b) a radiation-sensitive imaging layer over said planarizing underlayer.

12. (withdrawn) The structure of claim 11 wherein said layers are patterned such that portions of said substrate are exposed.

13. (original) The structure of claim 11 wherein said imaging layer is a silicon-containing resist.

14. (withdrawn) A method of forming a patterned material feature on a substrate, said method comprising:

(a) providing a material layer on a substrate,

(b) forming a planarizing layer over said material layer, said planarizing layer being formed by reacting a planarizing underlayer composition, said underlayer composition comprising

a polymer containing:

(i) cyclic ether moieties,

(ii) saturated polycyclic moieties, and

(iii) aromatic moieties, and

an acid generator,

(c) forming a radiation-sensitive imaging layer over said planarizing layer,

(d) patternwise exposing said imaging layer to radiation thereby creating a pattern of radiation-exposed regions in said imaging layer,

(e) selectively removing portions of said imaging layer and planarizing layer to expose portions of said material layer, and

(f) etching said exposed portions of said material layer, thereby forming said patterned material feature.

15. (withdrawn) The method of claim 14 further comprising:

(g) removing any remaining portions of said imaging layer and said

planarizing layer from material layer.

16. (withdrawn) The method of claim 14 wherein said radiation is ultraviolet radiation having a wavelength less than 200 nm.

17. (withdrawn) The structure of claim 14 wherein said imaging layer is a silicon-containing resist.

18. (withdrawn) The method of claim 14 wherein said material layer is selected from the group consisting of dielectric, metals, and semiconductors.

19. (withdrawn) A composition suitable for use as a planarizing underlayer in a multilayer lithographic process, said composition comprising:

(a) a polymer containing:
  (I) saturated polycyclic moieties, and
  (II) aromatic moieties,
(b) an acid generator, and
(c) a crosslinker.

20. (withdrawn) The composition of claim 19 wherein said polymer further comprises pendant hydroxyl moieties.

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